

Raymond T Tung

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

2,927
citations

840119

11
h-index

794141

19
g-index

20
all docs

20
docs citations

20
times ranked

3907
citing authors

#	ARTICLE	IF	CITATIONS
1	Quantitative explanation of the Schottky barrier height. <i>Physical Review B</i> , 2021, 103, .	1.1	10
2	Fermi level pinning for zinc-blende semiconductors explained with interface bonds. <i>Physical Review B</i> , 2021, 103, .	1.1	7
3	From NiSi ₂ experiments to density functional theory calculations: How the Schottky barrier mystery was solved. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	0.9	1
4	Bulklike band-offset mystery solved through energy minimization: Lessons from perovskite oxide heterojunctions. <i>Physical Review B</i> , 2019, 99, .	1.1	8
5	Charge Density and Band Offsets at Heterovalent Semiconductor Interfaces. <i>Advanced Theory and Simulations</i> , 2018, 1, 1700001.	1.3	20
6	Band offset formation at semiconductor heterojunctions through density-based minimization of interface energy. <i>Physical Review B</i> , 2016, 94, .	1.1	17
7	The physics and chemistry of the Schottky barrier height. <i>Applied Physics Reviews</i> , 2014, 1, .	5.5	931
8	Schottky barrier height systematics studied by partisan interlayer. <i>Thin Solid Films</i> , 2014, 557, 254-257.	0.8	10
9	Effect of metal interaction on the Schottky barrier height on adsorbate-terminated silicon surfaces. <i>Applied Surface Science</i> , 2013, 284, 720-725.	3.1	11
10	Modification of Schottky barrier height on Si (111) by Ga-termination. <i>Surface Science</i> , 2013, 610, 48-52.	0.8	7
11	Inhomogeneous ohmic contacts: Barrier height and contact area determination. <i>Applied Physics Letters</i> , 2012, 101, 051604.	1.5	12
12	Controlled modification of Schottky barrier height by partisan interlayer. <i>Solid State Communications</i> , 2011, 151, 1641-1644.	0.9	14
13	Bidirectional Control of Silicon's Surface Potential by Means of Molecular Coverage. <i>Journal of Physical Chemistry C</i> , 2010, 114, 18674-18678.	1.5	9
14	Tuning the Electrical Properties of Si Nanowire Field-Effect Transistors by Molecular Engineering. <i>Small</i> , 2009, 5, 2761-2769.	5.2	80
15	Controlling Au/n-GaAs junctions by partial molecular monolayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 3438-3451.	0.8	26
16	Controlling Semiconductor/Metal Junction Barriers by Incomplete, Nonideal Molecular Monolayers. <i>Journal of the American Chemical Society</i> , 2006, 128, 6854-6869.	6.6	102
17	Combined UHV and Liquid Phase (CULP) Processing of Self-assembled Nanostructures. <i>Materials Research Society Symposia Proceedings</i> , 2005, 879, 1.	0.1	0
18	Formation of an electric dipole at metal-semiconductor interfaces. <i>Physical Review B</i> , 2001, 64, .	1.1	275

#	ARTICLE	IF	CITATIONS
19	Recent advances in Schottky barrier concepts. Materials Science and Engineering Reports, 2001, 35, 1-138.	14.8	1,041
20	Chemical Bonding and Fermi Level Pinning at Metal-Semiconductor Interfaces. Physical Review Letters, 2000, 84, 6078-6081.	2.9	346